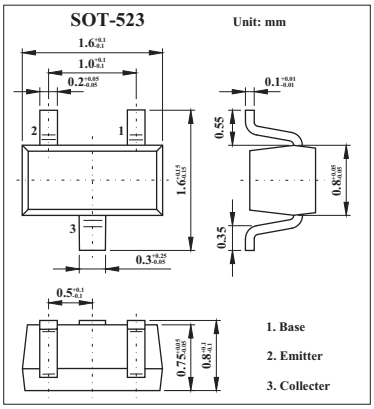
Low Frequency Transistor
2SA2018



■ Features

- A collector current is large
- Collector saturation voltage is low. $V_{CE(sat)} \leqslant 250mA$ at $I_C=200mA/I_B=10mA$

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	15	V
Collector-emitter voltage	V_{CEO}	12	V
Collector current	I_C	500	mA
	I_{CP} *	1	A
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

* Single pulse, Pw=1ms

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CBO}	I_C=10μA	15			V
Collector-emitter breakdown voltage	V_{CEO}	I_C=1mA	12			V
Emitter-base breakdown voltage	V_{EBO}	I_E=10μA	6			V
Collector cutoff current	I_{CBO}	V_{CB}=15V			100	nA
DC current gain	h_{FE}	V_{CE}=2V, I_C=10mA	270		680	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C/I_B=200mA/10mA		100	250	mV
Output capacitance	C_{ob}	V_{CB}=10V, I_E=0A, f=1MHz		6.5		pF
Transition frequency	f_T	V_{CE}=2V, I_E=10mA, f=100MHz		260		MHz

■ Marking

Marking	BW